

L424HDT BRIGHT RED	L424GDT GREEN
L424IDT HIGH EFFICIENCY RED	L424EDT ORANGE
L424SRDTSUPER BRIGHT RED	L424YDT YELLOW

### Features

- CYLINDRICAL TYPE, TOP DIFFUSED.
- LOW POWER CONSUMPTION.
- I.C. COMPATIBLE.
- RELIABLE AND RUGGED.
- LONG LIFE - SOLID STATE RELIABILITY.
- AVAILABLE ON TAPE AND REEL.

### Description

The Bright Red source color devices are made with Gallium Phosphide Red Light Emitting Diode.

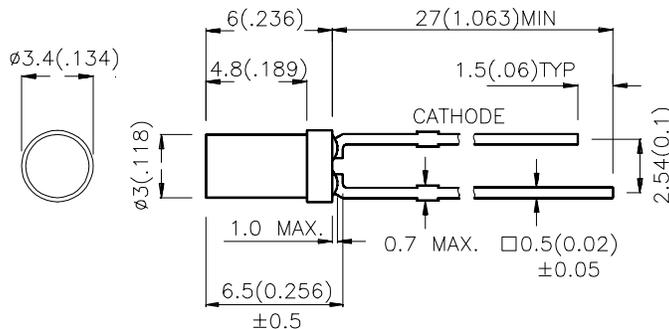
The High Efficiency Red and Orange source color devices are made with Gallium Arsenide Phosphide on Gallium Phosphide Orange Light Emitting Diode.

The Green source color devices are made with Gallium Phosphide Green Light Emitting Diode.

The Yellow source color devices are made with Gallium Arsenide Phosphide on Gallium Phosphide Yellow Light Emitting Diode.

The Super Bright Red source color devices are made with Gallium Aluminum Arsenide Red Light Emitting Diode.

### Package Dimensions



#### Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is  $\pm 0.25(0.01)$  unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

## Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) @ 10 mA * 20mA		Viewing Angle
			Min.	Typ.	2θ1/2
L424HDT	BRIGHT RED (GaP)	RED DIFFUSED	0.5	1	100°
L424IDT	HIGH EFFICIENCY RED (GaAsP/GaP)	RED DIFFUSED	3	5	100°
L424EDT	ORANGE (GaAsP/GaP)	ORANGE DIFFUSED	3	5	100°
L424GDT	GREEN (GaP)	GREEN DIFFUSED	1	4	100°
L424YDT	YELLOW (GaAsP/GaP)	YELLOW DIFFUSED	1	4	100°
L424SRDT	SUPER BRIGHT RED (GaAlAs)	RED DIFFUSED	*40	*100	100°

Notes:

1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.
2. \* Luminous intensity with asterisk is measured at 20mA.

## Electrical / Optical Characteristics at T<sub>A</sub>=25°C

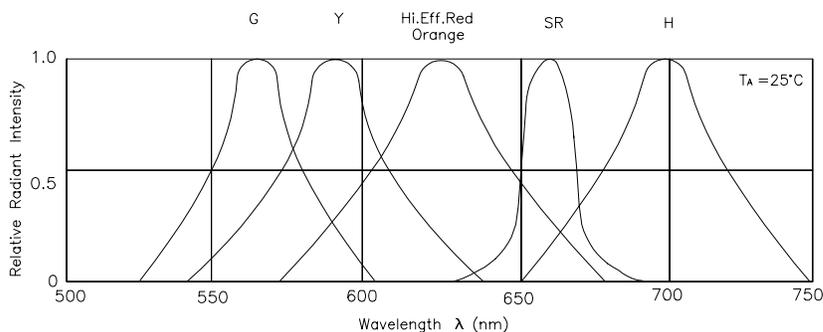
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ <sub>peak</sub>	Peak Wavelength	Bright Red High Efficiency Red Orange Green Yellow Super Bright Red	700 627 627 565 590 660		nm	IF=20mA
λ <sub>D</sub>	Dominate Wavelength	Bright Red High Efficiency Red Orange Green Yellow Super Bright Red	660 625 625 568 588 640		nm	IF=20mA
Δλ <sub>1/2</sub>	Spectral Line Halfwidth	Bright Red High Efficiency Red Orange Green Yellow Super Bright Red	45 45 45 30 35 20		nm	IF=20mA
C	Capacitance	Bright Red High Efficiency Red Orange Green Yellow Super Bright Red	40 15 15 15 20 45		pF	VF=0V;f=1MHz
V <sub>F</sub>	Forward Voltage	Bright Red High Efficiency Red Orange Green Yellow Super Bright Red	2.25 2.0 2.0 2.2 2.1 1.85	2.5 2.5 2.5 2.5 2.5 2.5	V	IF=20mA
I <sub>R</sub>	Reverse Current	All		10	μA	VR = 5V

## Absolute Maximum Ratings at $T_A=25^\circ\text{C}$

Parameter	Bright Red	High Efficiency Red	Orange	Green	Yellow	Super Bright Red	Units
Power dissipation	120	105	105	105	105	100	mW
DC Forward Current	25	30	30	25	30	30	mA
Peak Forward Current [1]	120	160	160	140	140	155	mA
Reverse Voltage	5	5	5	5	5	5	V
Operating/Storage Temperature	-40°C To +85°C						
Lead Solder Temperature [2]	260°C For 5 Seconds						

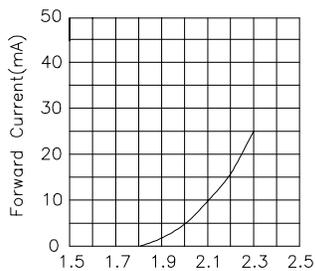
**Notes:**

- 1/10 Duty Cycle, 0.1ms Pulse Width.
- 4mm below package base.

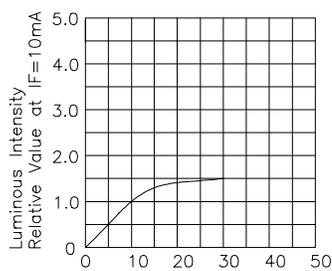


RELATIVE INTENSITY Vs. WAVELENGTH

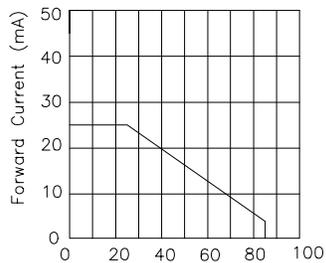
## Bright Red L424HDT



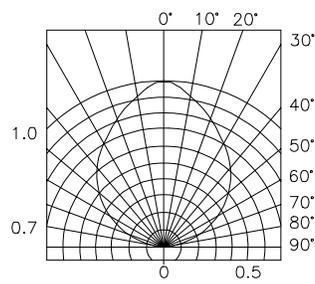
FORWARD CURRENT Vs. FORWARD VOLTAGE



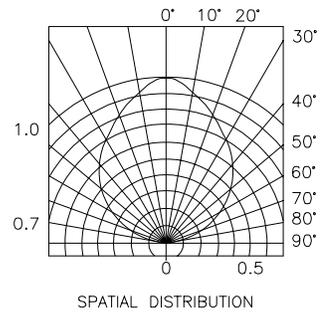
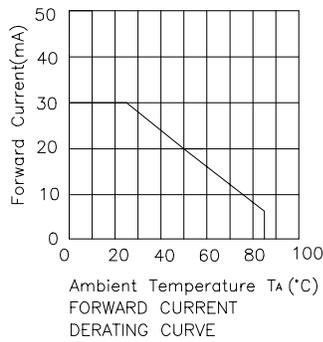
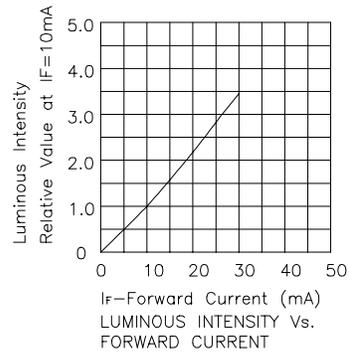
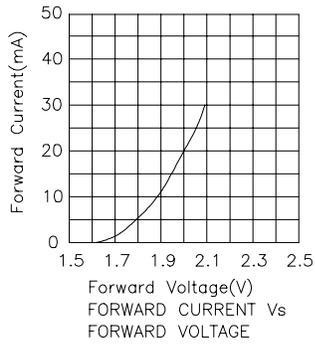
LUMINOUS INTENSITY Vs. FORWARD CURRENT



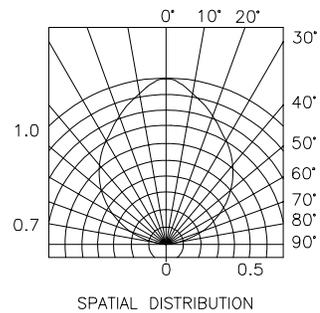
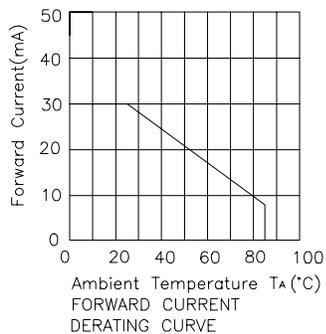
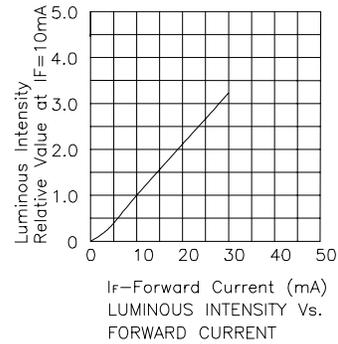
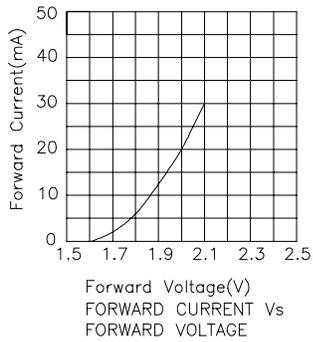
DERATING CURVE



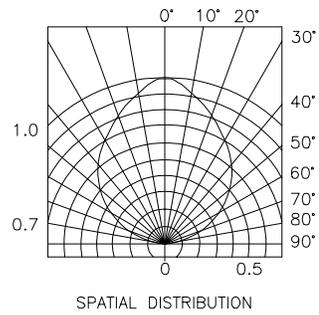
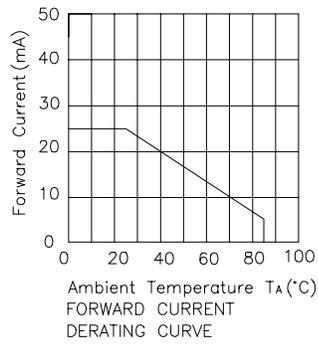
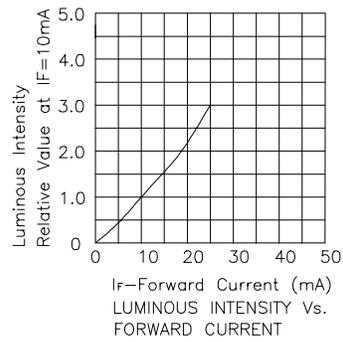
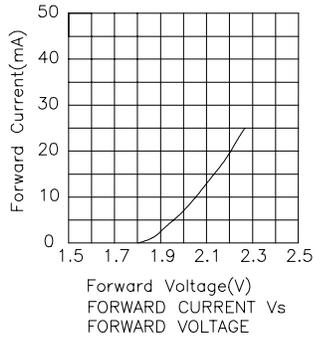
## High Efficiency Red L424IDT



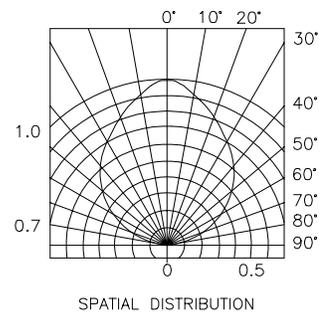
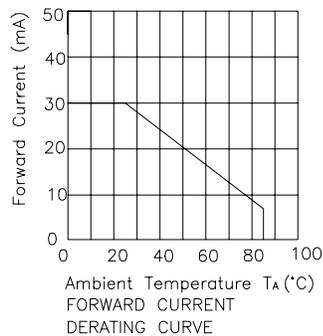
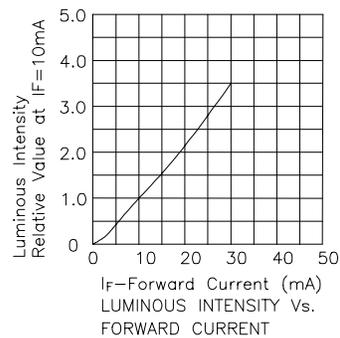
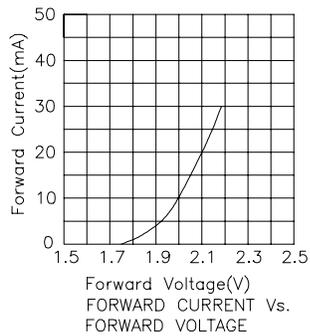
## Orange L424EDT



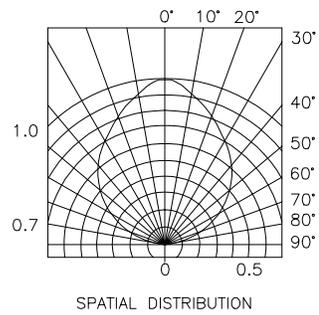
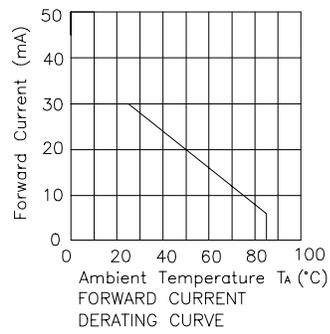
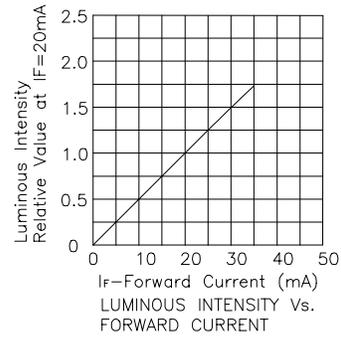
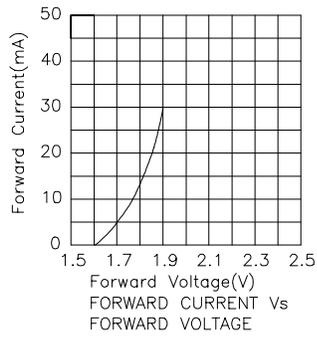
## Green L424GDT



## Yellow L424YDT



## Super Bright Red L424SRDT



## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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